RF Rx 2.6ghz Balun: Electrical Characteristics

Parameter	Unit	Test condition	RF Rx 2.6ghz Balun		
			Min	Тур	Max
Feature	TDD	/		Yes	
	Bypass	/		Yes	
★ Operating Frequency Ranges	MHz		2300		2900
★ Gain	dB	LNA On state		16.5	
		LNA Off state			
★ (Bypass on)	dB	Bypass On			
In band ripple/ every 100M	dB	/		0.5	
★Out Band Gain	dB	LNA On state			
★ Supply Current	Α	LNA On state		0.084	
		LNA Off state		0.01	
★Supply Voltage	V	LNA On state	3.15	3.3	3.45
		LNA Off state			
★ Input Power	dBm	LNA On state			25
		LNA Off state			
★Input Return Loss	dB	LNA On state,		-9.2	
		PVT			
		LNA Off state,			
		PVT			
		Bypass On, PVT			
★Output Return Loss	dB	LNA On state,		-9.5	
		PVT			
		LNA Off state,			
		Bypass On, PVT			
★ Noise Factor	dB	25°C/PVT		3	
★ Output P1dB	dBm	LNA On state,		17.5	
Cutput P1ab	abiii	PVT		17.5	
		Bypass On, PVT			
★Output IP3	dBm	LNA On state,		33	
		PVT			
		Bypass On, PVT			
Isolation (Pin≤20dBm)	dB	LNA Off state,			
		PVT			
Amplitude imbalance	dB	LNA On state,		0.5	
		PVT			
Phase imbalance	Deg	LNA On state,		4	
		PV			

Reverse isolation	dB	LNA On state,	30	
Enable Voltage	V	LNA On state,		0.5
		LNA Off state,	1.4	
		Bypass On, PVT		
		Bypass Off, PVT		
Enable Current	mA	276000 0,	0.05	0.25
Turn on time	us	LNA off 0		
(Vctrol 50%->90% RF out)		to		
		LNA on,PVT		
		Bypass on to LNA on,PVT		
		LNA on to		
		Bypass on		
		,PVT		
Turn on time	us	LNA off	1	
(Vctrol 50%->99% RF out)		to		
		LNA on,PVT Bypass on to		
		LNA on,PVT		
		LNA on to		
		Bypass on		
- · · · · ·		,PVT	0.4	
Turn off time	us	LNA on to	0.1	
(Vctrol 50%->10% RF out)		LNA off,PVT		
Turn off time	us	LNA on		
(Vctrol 50%->1% RF out)		to		
		LNA off,PVT		
Control Voltage True Table			0~0.5V o	
NA	dn	D) /T	1.4V~VDD	off
Maximum input power	dBm	PVT	25	
< 12G No oscillation Spur during on or off state.	dBm	PVT PVT	Yes No	
spar daring on or on state.	UDIII	FVI	glitch	
VSWR	/		gircii	
maximum Junction Temperature	°C	PV	150	l
★Operating Temperature Range	$^{\circ}$ C	PV	-40~105	
★ Storage Temperature Range	$^{\circ}$	Р	-60~150	
θ jc	$^{\circ}$	PV	14.2°C/W	
★ Lifetime at max. Tj	Years	PVT, on	10	
		state, offs		
		tate		
★ESD-HBM,	V	PVT, 500V	1000V	
for all pin				
ESD-CDM	V	PVT, 250V	500V	

★ MSL,	/	PVT, ≤MSL3	MSL2
Moisture Sensitive Level			
Package	mm*mm		2.1*2.1
Stress for device	N	Refer to	
		basestation	
		production	
		spec	
		Including top	
		pressure and	
		side pressure	
★ Reflow Requirement			TI doesn't reflow in
SMD package should do			the assembly flow
reflow(profile refer to J-STD-020D)			before ATE. Please
before ATE			follow J-STD_020D.
If the chip has done reflow during			
the assembly process, don't need to			
add reflow again			
No power up sequence rqmt			Yes

Parameters	Test or No	TI feedback
Frequency Range	must	No
(current leakage for power pin)	must	Yes
Gain	must	Covered for outliers
NF	must	No
Stability	must	Yes, large signal
		oscillations in band is
		covered
VSWR	must	No
OIP3	must	IMD3 Covered for
		outliers
OP-1dB	must	No